

Assignment 3

Ans: $V_{DD} = 5V$ $\cdot \left(\frac{W}{L}\right)_P = \left(\frac{W}{L}\right)_N$ $K'_n = 81 \mu A/V^2$
 $K'_p = 27 \mu A/V^2$
 $V_{th} = |V_{tp}| = 0.75V$

Assuming saturation mode for both transistors to calculate V_{out}

$$\frac{K_n}{2} (V_{GSN} - V_{th})^2 = \frac{K_p}{2} (|V_{GSP}| - |V_{tp}|)^2$$

$$\frac{1}{\left(\frac{K_p}{K_n}\right)} = \frac{(|V_{GSP}| - |V_{tp}|)^2}{(V_{GSN} - V_{th})^2}$$

Let $r = \frac{1}{\sqrt{\frac{K_p}{K_n}}} \Rightarrow r = \frac{|V_{GSP}| - |V_{tp}|}{V_{GSN} - V_{th}}$

$$r V_{GSN} - r V_{th} = V_{DD} - V_{GSN} - |V_{tp}|$$

$$(1+r) (V_{GSN}) = V_{DD} + r V_{th} - |V_{tp}|$$

$$V_{GSN} = \frac{V_{DD} + r V_{th} - |V_{tp}|}{1+r}$$

$$V_{GSN} = \frac{V_{DD} + \sqrt{\frac{K_n}{K_p}} V_{th} - |V_{tp}|}{1 + \sqrt{\frac{K_n}{K_p}}}$$

or $V_{GSN} = \frac{V_{DD} \left(\sqrt{\frac{K_p}{K_n}}\right) + V_{th} - \left(\sqrt{\frac{K_p}{K_n}}\right) |V_{tp}|}{1 + \sqrt{\frac{K_p}{K_n}}}$

Verification

for NMOS, $V_{gs} = V_{gd} = V_m \Rightarrow V_{ds} = V_m = V_{as}$

$$\therefore (V_{gs} > V_{gs} - V_{th})$$

↳ saturation

for PMOS; $V_{gs} = V_m = V_m \Rightarrow V_{sd} = V_{ds} - V_m$

$$V_{sd} = V_{ds} - V_m$$

$$\Rightarrow V_{ds} > |V_{gs}| - |V_{th}|$$

- satⁿ

Thus, we can safely take transistors to be in sat.

$$V_m = V_{gs} = V_{ds} \sqrt{\frac{K_p}{K_n}} + V_{th} - \sqrt{\frac{K_p}{K_n}} |V_{th}|$$
$$1 + \sqrt{\frac{K_p}{K_n}}$$

$$V_m = \frac{5 \sqrt{\frac{27}{81}} + 0.75 - 0.75 \sqrt{\frac{27}{81}}}{1 + \sqrt{\frac{27}{81}}}$$

$$= \frac{5 + 0.75 - 0.75}{\sqrt{3}}$$

$$1 + \frac{1}{\sqrt{3}}$$

$$= 2.031V$$

Ans 1) ϕ_{PLH} , At $A=0$, $V_{out}=0$, $V_{in}=0$
 \Rightarrow NMOS is in cutoff, PMOS is in sat $\Rightarrow V_{SG} = V_{DD}$

$$\therefore V_{SD} = V_{DD} > V_{SG} - (V_{TH})$$

Calculating \Rightarrow

$$I_{DP} = \frac{K_p}{2} (|V_{GS}| - V_{TH})^2 = \left(\frac{C_{ox} \mu_p}{2} \right) \frac{W}{L} (5-1)^2$$

$$= \frac{2 \times 10^{-5}}{2} (16) = 32 \times 10^{-5} \text{ A}$$

$$R_{V_{out}=0} = \frac{V_{DD} - V_{out}}{I_{DP}}$$

$$= \frac{5-0}{32 \times 10^{-5}} = \frac{10^5 \times 5}{32} = 1.5625 \times 10^4 \Omega$$

Calculating R @ $V_o = \frac{V_{DD}}{2}$ } Intermediate value of V_o
 $= \frac{V_{OH} + V_{OL}}{2}$

$$V_{in}=0 \quad = \frac{V_{DD} + 0}{2} = \frac{V_{DD}}{2}$$

\Rightarrow NMOS is in cutoff.

$$V_{SG} = V_{DD} - V_{in} = V_{DD} = 5V$$

\Rightarrow PMOS is linear mode. $(5 - (|V_{GS}| - |V_{TH}|) = 4)$

$$I_{DP} = K_p \left((V_{SG} - |V_{TH}|) V_{SD} - \frac{(V_{SD})^2}{2} \right)$$

$$= 4 \times 10^{-5} \left(4 \times \frac{5}{2} - \frac{(5/2)^2}{2} \right)$$

$$= 4 \times 10^{-5} \left(10 - \frac{25}{8} \right)$$

$$= 27.5 \times 10^{-5} \text{ A}$$

$$R_{V_{out}} = \frac{V_{DD}}{2} = \frac{V_{DD} - V_{out}}{I_{DP}} = \frac{2.5}{27.5 \times 10^{-5}}$$

$$= 0.0909 \times 10^5 \Omega \approx 9091 \Omega$$

$$R_{eq} = \frac{(15625 + 9091)}{2} = 12358 \Omega$$

$$\Rightarrow t_{in} = (0.69) \times R_{eq} \times C_L$$

$$= 0.69 \times 12358 \times 10^{-15}$$

$$= 8.527 \times 10^{-10} \text{ sec}$$

$$R_{pHL} \Rightarrow V_{in} = V_{DD}$$

$$V_{SM} = V_{DD} - V_{in} = 0$$

$$\Rightarrow V_{SM} < |V_{TP}| \Rightarrow \text{PMOS cutoff.}$$

$$\text{Ref } V_o = V_{DD} \Rightarrow$$

$$V_{GS} = V_{DD}$$

$$V_{DS} = V_{DD}$$

$$V_{GS} > V_{GS} - V_{TH}$$

$$\Rightarrow \text{NMOS is in sat}^{\text{th}} \text{ mode}$$

$$I_{DN} = \frac{\mu_n}{2} (V_{DD} - V_{TH})^2 = 2 \times 10^{-5} \times (5 - 2)^2$$

$$= \frac{64}{2} \times 10^{-5} \text{ A} = 32 \times 10^{-5} \text{ A}$$

$$R(V_o = V_{DD}) \Rightarrow \frac{V_{out}}{I_{DN}} = \frac{5}{32 \times 10^{-5}} = 15625 \Omega$$

$$R_{(V_{DS} = \frac{V_{DD}}{2})} \Rightarrow V_{in} = V_{DD} \\ \Rightarrow V_{SD} = 0 < |V_{TP}| \rightarrow \text{PMOS in cutoff mode}$$

$$V_{GS} = V_{DD} = 5V, \quad V_{DS} = \frac{V_{DD}}{2} = 2.5V \Rightarrow V_{GS} - V_{TN} = 4 > 2.5$$

\Rightarrow NMOS is in linear mode

$$I_{DN} = K_n \left((V_{GS} - V_{TN}) V_{DS} - \frac{V_{DS}^2}{2} \right) \\ = 4 \times 10^{-5} \left(4 \times 2.5 - \frac{2.5^2}{2} \right) \\ = 27.5 \times 10^{-5} \text{ A}$$

$$R_{(V_{DS} = \frac{V_{DD}}{2})} = \frac{V_{DS}}{I_{DN}} = \frac{2.5}{27.5 \times 10^{-5}} \\ = 0.0909 \times 10^5 \Omega = 9091 \Omega$$

$$R_{eq} \approx \left(\frac{15625 + 9091}{2} \right) \approx 12358 \Omega$$

$$t_{PHL} = 0.69 \times R_{eq} \times C_L \\ = 8.527 \times 10^{-10} \text{ sec}$$

$$t_p = \frac{t_{PHL} + t_{PLH}}{2} \\ = 8.527 \times 10^{-10} \text{ sec}$$

10) time calc.

V_{ds} goes from high to low
 V_{in} goes from low to high

$$\Rightarrow V_{in}(\theta = 0^\circ) = V_{DD}$$

$$V_{DS} - V_{TN} = 4V$$

So NMOS is in the satⁿ mode ($V_{DS} > V_{DS} - V_{TN}$)

For V_{in} from 5 to 4V and 0 mos is subthⁿ ($V_{GS} < 2V_{DS} - V_{TN}$)

$$I_{Dn} = \frac{\mu_n}{2} (V_{DS} - V_{TN})^2$$

$$= 3.2 \times 10^{-4} A$$

$$\text{time from 5 to 4V} \Rightarrow \frac{C \Delta V}{I_{Dn}} = \Delta t \Rightarrow \Delta t = 3.12 \times 10^{-8} s$$

for V_{in} from 4 to 0V

$$\text{At } V_{in} = \frac{V_{DD}}{2} \Rightarrow \text{NMOS in linear mode}$$

$$(V_{DS} < V_{DS} - V_{TN})$$

$$2.5V < 4V$$

$$I_{Dn} = \frac{\mu_n}{2} \left[(V_{DS} - V_{TN}) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

$$= \frac{\mu_n}{2} \left(4 \times 2.5 - \frac{2.5^2}{2} \right) = 2.75 \times 10^{-4} A$$

$$I_{av} = 2.915 \times 10^{-4} A = \left(\frac{3.2 + 2.75}{2} \right) \times 10^{-4}$$

time delay from 4V to 2.5V

$$\Rightarrow \int C dV = \int C I_{av} = \frac{C(4-2.5)}{2.915 \times 10^{-4}} = \Delta t$$

$$\Delta t \approx 5.04 \times 10^{-10} \text{ sec}$$

$$\Rightarrow t_{PHL} = 8.165 \times 10^{-10} \text{ sec}$$

$$A_{PLH} \text{ soln} \Rightarrow V_{in}(0^+) = 0V \Rightarrow \text{NMOS in cutoff} \\ (V_{GS} < V_{th})$$

V_{out} from 0V to 1V gives
 \Rightarrow pmos in soln

$$V_{SD} > V_{GS} - |V_{TP}| = 4V$$

$$I_{DP} = K_P (V_{GS} - |V_{TP}|)^2 = 3.2 \times 10^{-4} A$$

$$\Delta t \text{ for } 0 \text{ to } 1V \Rightarrow \frac{C \Delta V}{\Delta t} = I_{DP} \Rightarrow \Delta t = 3.225 \times 10^{-10} \text{ sec}$$

$$\text{for } 1V \text{ to } \frac{V_{DD}}{2} \Rightarrow \text{pmos in linear region} \\ (V_{SD} < 4V = V_{GS} - V_{TP})$$

$$\Rightarrow I_{DP} = K_P \left((V_{GS} - |V_{TP}|) V_{SD} - \frac{V_{SD}^2}{2} \right)$$

$$I_{DP} \approx 2.75 \times 10^{-4} A$$

$$\Delta t \text{ from } 1V \text{ to } 2.5V \Rightarrow \frac{C \Delta V}{\Delta t} = I_{av}$$

$$\frac{C \Delta V}{\Delta t} = \frac{2.75 \times 3.2}{2 \times 10^{-4}}$$

$$\Rightarrow \Delta t = 5.04 \times 10^{-10} \text{ sec}$$

$$\Rightarrow t_{PLH} \approx 8.165 \times 10^{-10} \text{ sec}$$

$$\Rightarrow t_p = \frac{t_{PLH} + t_{PHL}}{2} \approx 8.165 \times 10^{-10} \text{ sec}$$

$$\Rightarrow [t_p = t_{PLH} = t_{PHL}] =$$

t_{pLH} = time for V_{out} goes from V_{OL} to V_{OH} at $\left(\frac{V_{OH} + V_{OL}}{2}\right)$ or $\frac{V_{DD}}{2}$

At $t = 0^+$ $V_{in} = 0V$
 $V_{out} = 0V$

$V_{GS} = V_{DD}$, $V_{SD} = V_{DD}$

$V_{SD} > V_{GS} - |V_{TP}|$

\Rightarrow sat. mode for PMOS

Magnitude of current I_D through PMOS

$= \frac{k_p}{2} (V_{GS} - |V_{TP}|)^2$

$= 2 \times 10^{-5} (5-2)^2$

$= 0.32 \text{ mA}$

NA $V_{out} = 2.5V$

$V_{in} = 0V$

$\Rightarrow \begin{cases} V_{GS} = 5V \\ V_{SD} = 2.5V \end{cases}$

$V_{GS} - |V_{TP}| > V_{SD}$

\Rightarrow PMOS is linear

(NMOS in cutoff)
 $V_{GS} < V_{TN}$

Mag of I_D flowing $= k_p \left((V_{GS} - |V_{TP}|) V_{SD} - \frac{V_{SD}^2}{2} \right)$

$= 10^{-5} \times 4 \left(4 \times \frac{5}{2} - \frac{2.5^2}{2} \right)$

$= 2.75 \times 10^{-4} = 0.275 \text{ mA}$

$I_{avg} = \frac{0.275 + 0.32}{2} \text{ mA}$

$= 0.2975 \text{ mA}$

We know $C_L \frac{dV_o}{dt} = I_{av}$

$$\Rightarrow C_L \left(\frac{V_{DD}}{2} - V_{OL} \right) = t_{PLH} I_{av}$$

$$\Rightarrow \frac{10^{-13} (2.5)}{0.2925 \times 10^{-3}} = t_{PLH}$$

$$t_{PLH} = 8.4034 \times 10^{-10} \text{ sec}$$

for PMOS \Rightarrow At $\theta = 0^\circ$, $V_{in} = V_{DD} = 5V$
 $V_{out} = 5V$

$|V_{in}| < |V_{TP}| \Rightarrow$ PMOS is off

for NMOS, $V_{GS} = V_{DD}$, $V_{DS} = V_{DD} \Rightarrow V_{DS} > V_{GS} - V_{TN}$
 \Rightarrow NMOS is on

$$I_D = \frac{K_n}{2} (V_{GS} - V_{TN})^2 = 0.52 \text{ mA}$$

At $V_{out} = \frac{V_{DD}}{2}$, $V_{in} = V_{DD} = 5V$
 $V_{out} = 2.5V$

$|V_{in}| < |V_{TP}| \Rightarrow$ PMOS is on

for NMOS, $V_{GS} = V_{DD}$, $V_{DS} = \frac{V_{DD}}{2} = 2.5V$
 \Rightarrow NMOS is on $(V_{GS} - V_{TN} > V_{DS})^2$

$$I_D = K_n \left((V_{GS} - V_{TN}) V_{DS} - \frac{V_{DS}^2}{2} \right)$$

$$= K_n (4 \times 2.5 - \frac{2.5^2}{2}) = 0.275 \text{ mA}$$

$$I_{avg} = \frac{0.275 + 0.52}{2} \text{ mA} = 0.2975 \text{ mA}$$

$$C_L \frac{dV_o}{dt} = I_{avg} \Rightarrow C_L \frac{2.5}{I_{avg}} = t_{PHL} \Rightarrow t_{PHL} = 8.4034 \times 10^{-10} \text{ sec}$$

$$t_p = t_{PHL} + t_{PLH} = 8.4034 \times 10^{-10} \text{ sec}$$

~~Values differ in (i) and (ii) due to different values in~~

A_{PLH}

t_{PLH}

θ_p

i) $8.521 \times 10^{-9} \text{ s}$

$8.52 \times 10^{-9} \text{ s}$

$8.521 \times 10^{-9} \text{ s}$

ii) $8.165 \times 10^{-10} \text{ s}$

$8.165 \times 10^{-10} \text{ s}$

$8.165 \times 10^{-10} \text{ s}$

iii) $8.4034 \times 10^{-10} \text{ s}$

807.3 ps

$8.4034 \times 10^{-10} \text{ s}$

Ans 3

Assuming V_{in} as step input from high to low.

$\rightarrow V_{in} = 0 \text{ V}$

$(5 \text{ V} \rightarrow 0 \text{ V})$

We know, $t_{PLH} = (\ln 2) C_L R_{eq}$

$= 2.2 C_L R_{eq}$

Here, $R_{eq} = \frac{R_{(10\%)} + R_{(90\%)}}{2}$

(a) $10\% \rightarrow V_{out} = 0.1 V_{DD} = 0.5 \text{ V}$

$V_{in} = 0 \rightarrow$ NMOS in sat^n

$\Rightarrow V_{in} = V_{GS} = 0 < V_{TH} = 1 \text{ V}$

$V_{SDN} = V_{DD} - V_{in} = 5 \text{ V}$

$V_{SDP} = V_{DD} - V_{out} = 4.5 \text{ V}$

$V_{SDP} = 4.5 > V_{SDN} - |V_{TP}| = 4 \text{ V}$

\Rightarrow PMOS is in sat^n

$I_{DP} = \frac{\mu_p}{L} (V_{SDN} - |V_{TP}|)^2 = 32 \times 10^{-5} \text{ A}$

$$R(A=10\%) = \frac{V_{DD} - V_{out}}{I_{DP}} = \frac{4.5}{82 \times 10^{-5}} = 14062.5 \Omega$$

@ 90% $\Rightarrow V_{out} > 4.5V, V_{in} = 0$

NMOS in cutoff ($\because V_{GS} = 0 < V_{th} = 1V$)

for PMOS, $V_{SG} = V_{DD} - V_{in} = 5V$

$$V_{SG} - |V_{TP}| = 4V > V_{SD} = 0.5V$$

PMOS in linear mode.

$$R(A=90\%) = \frac{V_{DD} - V_{out}}{I_{DP}} = \frac{0.5}{K_P (V_{SG} + V_{TP}) V_{SD} - \frac{V_{SD}^2}{2}}$$

$$R(A=90\%) = \frac{0.5}{4 \times 10^{-5} \left((5-2) \frac{1}{2} - \frac{1}{8} \right)}$$

$$= 66666 \Omega$$

$$R_{eq} = \frac{14062.5 + 66666 \Omega}{2}$$

$$= 10364.583 \Omega$$

$$t_{TLH} = 2.2 \times 0.1 \times 10^{-12} \times (10364.583)$$

$$= 2.28 \times 10^{-9} \text{ seconds}$$

$$= 2.28 \text{ ns}$$

$t_{THL} \Rightarrow$ Assuming V_{in} as step i/p from low to high.

$$\Rightarrow V_{in} = 5V \quad (0V \rightarrow 5V)$$

$$t_{THL} = 2.2 C_L R_{eq}$$

$$R_{eq} = R_{90\%} + R_{10\%}$$

@ 90% $V_{out} = 4.5 \text{ V}$
 $V_{in} = 5 \text{ V}$

for PMOS $\Rightarrow V_{SG} = 0 < |V_{TP}| \rightarrow \text{Cutoff}$

for NMOS $\Rightarrow V_{GS} = 5 \text{ V}$

$V_{GD} = V_{GS} - V_{TN} = 4 \text{ V} < V_{DS} = 4.5 \text{ V}$

\rightarrow Sat mode

$$I_{DN} = \frac{K_N}{2} V_{GD}^2 = \frac{20 \times 10^{-6}}{2} \times 16 = 32 \times 10^{-5} \text{ A}$$

$$R_{90\%} = \frac{V_{out}}{I_{DN}} = \frac{4.5}{32 \times 10^{-5}} = 14062.5 \Omega$$

@ 10% $\Rightarrow V_{out} = 0.5 \text{ V}$
 $V_{in} = 5 \text{ V}$

for PMOS $\Rightarrow V_{SG} = 0 < |V_{TP}| \rightarrow \text{Cutoff}$

NMOS $\Rightarrow V_{GS} = 5 \text{ V}$

$V_{GD} = 4 \text{ V} > 0.5 \text{ V} = V_{DS}$

\rightarrow Linear mode.

$$I_{DN} = K_N \left(V_{GD} V_{DS} - \frac{V_{DS}^2}{2} \right)$$

$$= K_N \left(4 \times \frac{1}{2} - \frac{1}{8} \right) = 7.5 \times 10^{-5}$$

$$R_{10\%} = \frac{V_{out}}{I_{DN}} = \frac{0.5}{7.5 \times 10^{-5}} = 6666.6 \Omega$$

$$R_{eq} = 10364.583 \Omega$$

$$A_{THL} = 2.0 \times R_{eq} \times C_L = ?$$

$P_{THL} = P_{TLH}$ as expected from symmetry of CMOS

Q4. $I_{sc\ max}$ occurs at $V_{in} = V_{out}$ (when both mosfets are in satⁿ)

for NMOS, $V_{in} = V_{out} = V_{in} = V_{out}$
 $V_{gs} = V_{in} > V_{th} - V_{th} \Rightarrow \text{sat}^n$

for PMOS, $V_{in} = V_{out} = V_{in}$

$$\Rightarrow V_{sd} = V_{DD} - V_{in}$$

$$V_{sd} = V_{DD} - V_{in} > V_{th} - |V_{th}| \rightarrow \text{saturation}$$

$$\frac{K_n}{2} (V_{gs} - V_{th})^2 = \frac{K_p}{2} (V_{sd} - |V_{th}|)^2$$

$$(V_{in} - 1)^2 = (V_{DD} - V_{in} - 1)^2$$

$$(V_{in} - 1)^2 = (V_{DD} - V_{in} - 1)^2$$

$$\Rightarrow V_{in} = \frac{V_{DD}}{2} = 2.05\text{ V}$$

$$I_{sc\ max} = \frac{K_n}{2} (V_{in} - 1)^2 = \frac{K_n}{2} (2.05 - 1)^2$$

$$= 4.5 \times 10^{-5}\text{ A}$$

(P_{sc}) Power dissipated = $\alpha_{0-2} + P_{sc}$

$$\text{also } P_{sc} = V_{DD} I_{sc\ max} = \frac{1}{2} V_{DD} I_{sc\ max} \left(\frac{f_{clk}}{0.3} \right) \left(\frac{V_{DD} - V_{th} - |V_{th}|}{V_{DD}} \right)$$

$$= \frac{1}{2} \times 4.05 \times 10^{-5} (f_{clk} + f_f) (3)$$

$$P_{dynamic} = \alpha_{0-2} + C_L V_{DD}^2 \quad | \quad P_{sc} = \alpha_{0-2} \cdot P_{sc\ set}$$

Given condition: $P_{sc} < 0.1 P_{dynamic}$

$$\alpha_{0 \rightarrow 1} f_{SL} < \alpha_{0 \rightarrow 1} \times f_p (C_L V_{DD}^2 \times 0.1)$$

Taking $t_r + t_f = 2t_s$ gives \Rightarrow

$$\frac{9.5}{2} \times 10^{-5} (2t_s) \times 3 < C_L V_{DD}^2 \times 0.1$$

$$\Rightarrow t_s < \cancel{2.41 \text{ ns}} \quad \cancel{2.41 \text{ ns}}$$

$$t_s < \underline{1.84 \text{ ns}}$$

Ans

Ans

Ans

Ans

$$V_{th} = |V_{tp}| = 0.6V$$

$$V_{th}' = 400 \mu A, \quad K_p' = 200 \mu A V^{-2}$$

1) For $V_{out} = V_{on} = V_{op} = 2.5V$

PMOS is in cutoff ($V_{gs} < |V_{tp}|$)

$$\Rightarrow I_{Dp} = 0$$

Static Power dissipation $\Rightarrow V_{DD} \times I_{Dp} = 0$

2) $V_{out} = V_{on} = 0V$

NMOS is in cutoff ($V_{gs} < V_{th}$)

$$\Rightarrow I_{Dn} = 0$$

$$\Rightarrow V_{DD} \times I_{Dn} = 0$$

\Rightarrow Static Power Dissipation ≈ 0

\Rightarrow Avg Static Power dissipation ≈ 0

3) for transition of V_{out} from lower to high

\Rightarrow NMOS is in \otimes cutoff

\Rightarrow PMOS is in operating regime

Avg Din Power dissipation = $\frac{K_{on}}{T} \times C_L \times V_{supply} \times V_{swing}$

$$= 0.01 \times 235 \times 10^6 \times 6 \times 10^{-15} \times 3 \times 2.5$$

$$= 0.01 \times 235 \times 10^6 \times 10^{-15} \times 3 \times 2.5$$

$$= 44.06 \mu W$$

We already know that when V_{out} goes from high to lower there is no current I_{Dp} PMOS is in cutoff

no dynamic power dissipation for this transition

Q.1) $t_r = 1 \text{ ns}$ $t_f = 1.5 \text{ ns}$

$$P_{sc} = \text{Cross rate } V_{DD} \frac{1}{2} \left(\frac{t_r + t_f}{0.8} \right) \left(\frac{V_{DD} - V_{Th} - |V_{Tp}|}{V_{DD}} \right)$$

We know, I_{smax} occurs when
 $V_{in} = V_{in}$

\Rightarrow Both mosfets are in satⁿ

\therefore for PMOS $\Rightarrow V_{SD} = V_{DD} - V_{in} > V_{SG} - |V_{Tp}|$
 \Rightarrow satⁿ.

for NMOS $\Rightarrow V_{DS} = V_{in} > V_{GS} - V_{Th}$
 \Rightarrow satⁿ.

$$\frac{K_n}{2} (V_{DD} - V_{in})^2 = \frac{K_p}{2} (V_{SG} - |V_{Tp}|)^2$$

$$\frac{K_n}{2} \left(\frac{w}{L} \right)_N (V_{in} - 0.5)^2 = \frac{K_p}{2} \left(\frac{w}{L} \right)_P (2.5 - V_{in} - 0.6)^2$$

for NMOS we take min value of ω/L

$$\left(\frac{w}{L} \right)_N = 400 \frac{\mu A}{V^2} = \left(\frac{w}{L} \right)_N$$

Also $\left(\frac{w}{L} \right)_P = \beta \left(\frac{w}{L} \right)_N = 2 \left(\frac{w}{L} \right)_N$

$$\begin{aligned} K_p' \left(\frac{w}{L} \right)_P &= 200 \frac{\mu A}{V^2} \left(\frac{w}{L} \right)_P \\ &= 400 \frac{\mu A}{V^2} \left(\frac{w}{L} \right)_N \end{aligned}$$

$\Rightarrow K_p = K_N$

$$(V_m - 0.6)^2 = (V_m - 0.9)^2$$

$$\Rightarrow (V_m = 1.25 \text{ V})$$

$$I_{scmax} = \frac{R_{in}}{2} \times \left(\frac{C_{in}}{L_{in}} \right) \times (1.25 - 0.6)^2$$

$$= \frac{400 \times 10^{-6}}{2} (0.4225) \frac{\omega_{min}}{L_{min}}$$

$$= 8.45 \times 10^{-5} \times \frac{\omega_{min}}{L_{min}}$$

$$\text{for } \omega_{min} = L_{min} \Rightarrow I_{sc} = 8.45 \times 10^{-5} \text{ A}$$

$$P_{sc} = 0.01 \times 235 \times 10^{-6} \times 2.5 \times \frac{1}{2} \left(\frac{1+1.5}{2.0} \right) \times \frac{1.2}{2.5} \times I_{scmax}$$

$$= 0.01 \times 2.5 \times 235 \times 10^{-6} \times \frac{2.5}{2} \left(\frac{1.5}{2.5} \right) \times 8.45 \times 10^{-5} \times \frac{\omega_{min}}{L_{min}}$$

$$= 4.0325 \times 10^{-7} \frac{\omega_{min}}{L_{min}} \text{ watt}$$

$$\text{for } \omega_{min} = L_{min} \cdot \boxed{P_{sc} = 0.4 \mu \text{ W}}$$

Ans $C_{gr} = r(1+\beta)(g_0$
 $= 36g_0 = 3 \times 10^{-11} \text{ P}$

$$C_L = 1 \text{ pF}$$

$$f = e(1 + r/A)$$

$$\ln f = 1 + \frac{r}{f} = 1 + \frac{1}{f} \quad (r \approx 1)$$

Consider 1^{st} $\Rightarrow L(f) = \ln f - 1 - \frac{1}{f}$

$$L(f) = \ln f - \frac{1}{f} - 1 = 0$$

Take initial value of f_0 as 2.5

$$\ln f_0 = 1 + \frac{1}{f_0}$$

$$\ln f_0 = 1 + \frac{1}{2.5} = 1.28571$$

$$\Rightarrow f_0 = 3.61725$$

Now for II iteration $\Rightarrow \ln f_0 = 1 + \frac{1}{3.61725} \approx 1.27641$

$$f_0 = 3.5820$$

Now for III iteration $\Rightarrow \ln f_0 = 1 + \frac{1}{3.5820} \approx 1.27839$

$$\Rightarrow f_0 = 3.5931$$

IV iteration $\Rightarrow f_0 = 3.59057$

V iteration $\Rightarrow f_0 = 3.59127$

VI iteration $\Rightarrow f_0 = 3.591028$

NI Iteration $\Rightarrow f_0 = 3.5912$

VTI Iteration $\Rightarrow f_0 = 3.5922$

$f_0 = 3.5911$

$\Rightarrow f = 3.5911$

$$N = \frac{\ln(F)}{\ln f} \Rightarrow N = \frac{\ln(100/3)}{\ln f} = \frac{\ln(1000/3)}{\ln(3.5911)}$$

$\left[\text{where } P = \frac{C_1}{C_2} = \frac{C_L}{C_2(1+f)^N} \right] N = 4.54$
 $N = 4 \text{ } \underline{\underline{\text{Ans}}}$

$$A_p = N A_p \left(1 + \frac{f}{2} \right) = 4 A_p \left(1 + \frac{4.2722}{2} \right) = 21.09 A_p$$

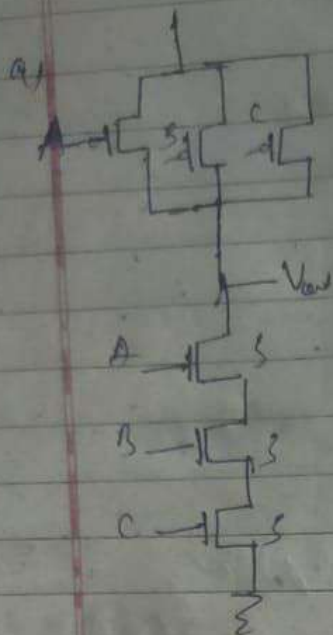
ii) $N = 5, P = \frac{C_1}{C_2} = \frac{10^{-12}}{10^{-15} \times (1+f)^N} = \frac{1000}{5}$

$$f = P^{1/N} = \left(\frac{1000}{5} \right)^{1/5} = 3.0196$$

$$\begin{aligned}
 A_p &= N A_p \left(1 + \frac{f}{2} \right) \\
 &= 5 A_p \left(1 + \frac{3.0196}{2} \right) \\
 &= 20.098 A_p
 \end{aligned}$$

Case (i) ~~has~~ has a bit smaller delay than (ii)

Ans 7.) NAND (1/m 3 i/p) o/p = \overline{ABC}
 $= \overline{A} + \overline{B} + \overline{C}$



$$Size = 5(5A_0) + 3(5A_0)$$

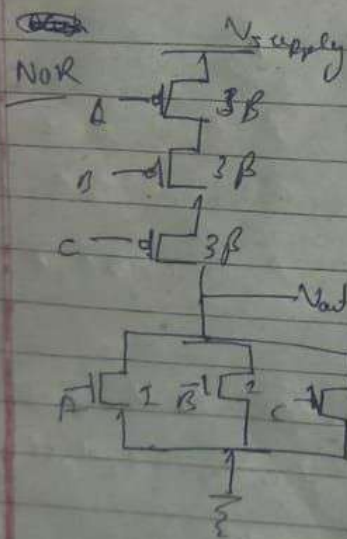
$$= 3(5A_0) + 9A_0$$

$$= 9A_0 + 9A_0$$

$$or = 3(3 \times 5) A_0$$

$$= 16.5 A_0$$

each PMOS is β scaled and each NMOS is β scaled



$$o/p = \overline{A+B+C}$$

$$= \overline{A} \cdot \overline{B} \cdot \overline{C}$$

each PMOS is 3β scaled

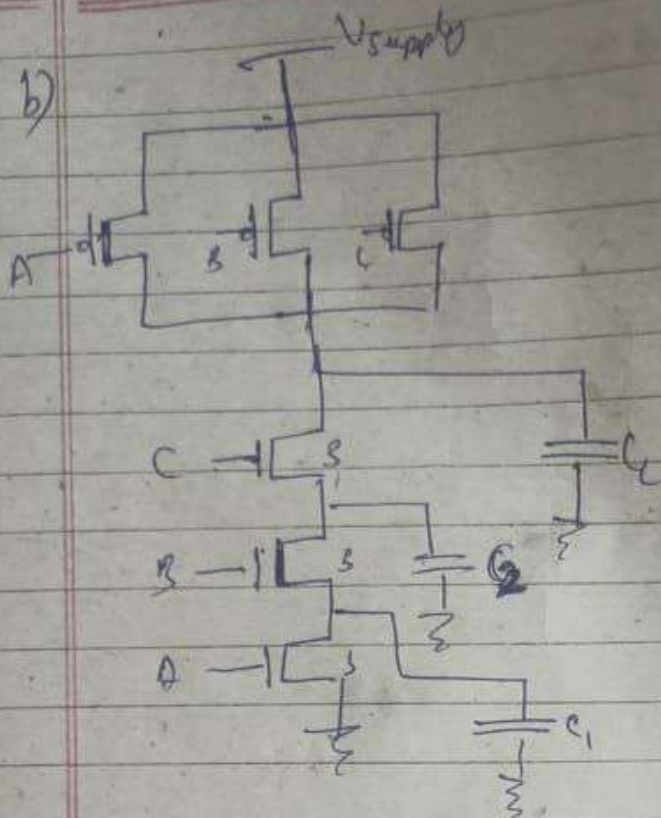
each NMOS is unity scaled

$$Size = 3 \times 3A_0 + 3 \times 1A_0$$

$$= 9A_0 + 3A_0$$

$$= 3A_0(3\beta + 1) = 25.5 A_0$$

NAND



Note \rightarrow To get C_L, C_2, C_1 , we focus on neighbouring transistors

$$\Rightarrow C_L = 3\gamma C_{g0} + 3\alpha\beta\gamma C_{g0}$$

$$= 3\gamma(1+\beta)C_{g0}$$

$$= 3 \times 1.05(3.5) \times 10^{-15}$$

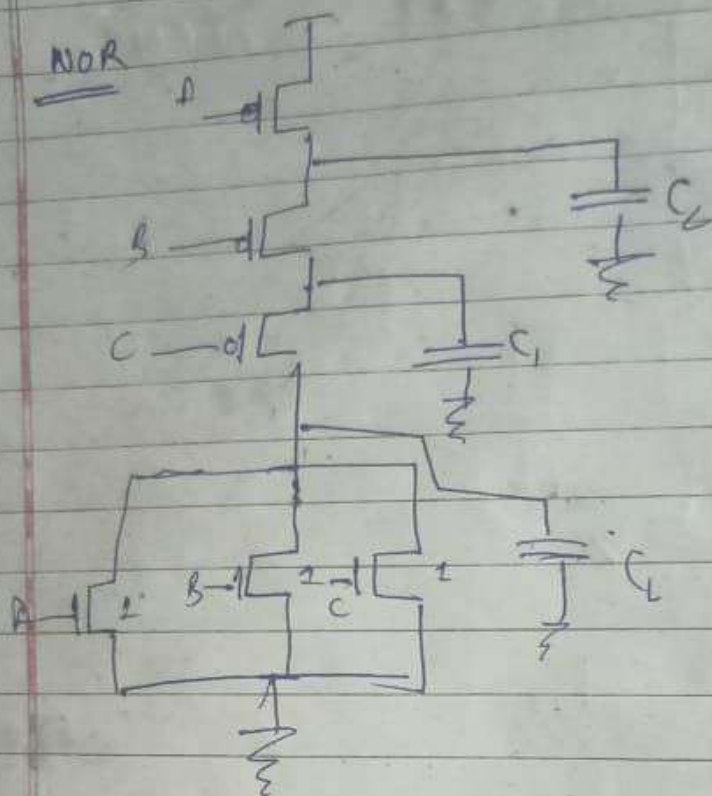
$$= 11.025 \text{ fF}$$

$$C_1 = 3\gamma C_{g0} + 3\gamma C_{g0}$$

$$= 6\gamma C_{g0}$$

$$= 6.3 \text{ fF}$$

$$C_2 = 3\gamma C_{g0} + 3\gamma C_{g0} = 6\gamma C_{g0} = 6.3 \text{ fF}$$



$$C_2 = 3\alpha \tau C_{g0} + 3\beta \tau C_{g0}$$

$$= 3\tau C_{g0} (1 + \beta)$$

$$= 11.025 \text{ fF}$$

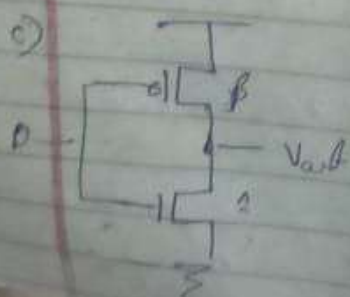
$$C_1 = 3\beta \tau C_{g0} + 3\beta \tau C_{g0}$$

$$= 6\beta \tau C_{g0}$$

$$= 15.75 \text{ fF}$$

$$C_2 = 3\beta \tau C_{g0} + 2\beta \tau C_{g0} = 6\beta \tau C_{g0}$$

$$= 15.75 \text{ fF}$$



Inverter

$$I_{DC} = I_{A0} + I_{A1}$$

$$= (\beta + 1) I_{A1} = 3.5 \text{ A}$$

Worst case delay for inverter \Rightarrow

$$t_{PLH} = (0.2) (R_{eq}) (C_L) = 0.69 \times (1 \text{ M}) (C_{gs}) R_{eq}$$

$$= 2.53575 \text{ ns Req/sec}$$

$$t_{PHL} = 0.69 \times R_{eq} C_L = 0.69 \times R_{eq} \times (1 \text{ M}) C_{gs}$$

$$= 2.53575 \text{ ns Req/sec}$$

Worst case power dissipation $= \alpha_{0 \rightarrow 1} f \times C_L V_{DD}^2$

$$= \alpha_{0 \rightarrow 1} f \times (C_{gs} + C_{gd}) \times V_{DD}^2$$

For $P_A = \frac{1}{2} \Rightarrow P_{avg} = \frac{1}{4} \times f \times (10^{-15}) (3.57) (V_{DD}^2)$

$$= 8.26375 \text{ nW} \times 10^{-15} \text{ W}$$

$$t_p = \frac{t_{PLH} + t_{PHL}}{2} = 2.53575 \text{ ns Req/sec}$$

NAND Area $= 3 \text{ M} (p \times b)$

Worst case delay,

Using ~~Equivalent~~ delay,

$$t_{PHL} = (0.69) \left(\frac{R_{eq} \times C_L \times \left(\frac{R_{eq} + R_{eq}}{3} \right) \left(C_{gs} + \left(\frac{R_{eq} + R_{eq} + R_{eq}}{3} \right) C_L \right) \right)$$

$$= 11.954 \text{ ns Req/sec}$$

$$A_{PLH} = 0.65 \text{ Reg } C_L$$

$$= 0.65 \text{ Reg } 11.025 \times 10^{-15}$$

$$= 7.6072 \text{ pReg } \text{Sec}$$

$$t_p = 9.78 \text{ Reg } \text{Sec}$$

Worst case Power dissipation $\Rightarrow P_{stat} = 0$, so we

need

Polynomial for worst

A B C E

Case dynamic power

1 1 1 0

dissipation when A=B=1 and

1 1 0 2

C goes from 1 to 0.

1 0 1 2

0 1 1 2

$P_{worst} = P_{dynamic}$

0 0 2 2

1 0 0 2

$$= f P_A P_B P_C (P_A P_B (1 - P_C))$$

0 1 0 2

$$+ (C_L V_{DD}^2 + C_2 (V_{DD} - V_{th})^2)$$

0 0 0 2

$$+ C_1 (V_{DD} - V_{th}) V_{DD}$$

$$= f P_A^2 P_B^2 P_C (1 - P_C)$$

$$+ (99.225 + 2(1 - 50\mu))$$

$$P_{worst} = f P_A^2 P_B^2 P_C (1 - P_C) (99.225 + 12.6(9 - 3V_{th}))$$

(NANO)

To get worst value, assuming $P_A = P_B = 1, P_C = \frac{1}{2}$

$$P_{worst} = f (53.156 \mu - 9.41 V_{th})$$

$$\text{NBR } P_{area} = P_A (2 + 9B)$$

$$\text{Worst case } A_{PLH} = 0.65 \left(\frac{R_{eq1} + C_2}{3} + \left(\frac{R_{eq1} + R_{eq2}}{3} \right) \right. \\ \left. + \left(\frac{R_{eq2} + R_{eq3}}{3} + \frac{R_{eq3}}{3} \right) C_L \right)$$

$$= 18.475 \text{ Reg } \text{Sec}$$

Worst case

$$k_{pnl} \Rightarrow k_{pnl} = 0.69 \text{ Reg } \times C_L$$

$$= 7.6072 \text{ Reg free}$$

$$A_p = 13 \text{ Reg free}$$

Worst case Power dissipation $\Rightarrow P_{ds} = 0$, so we need to get P_{dyn}

Refer NOR diagram

Worst = Polymorphic \Rightarrow about occur
when $A = g_{kns}$
to $A = 0$
and $B = C = 0$

A	B	C	F
1	1	1	0
1	1	0	0
1	0	1	0
0	1	1	0
0	0	1	0
1	0	0	0
0	1	0	0
0	0	0	1

$$P_{\text{Worst}} = f P_A P_B P_C (C_1 - P_A) P_B P_C$$

$$\times (C_L V_{DD}^2 + C_1 V_{DD} (V_{DD} - |V_{tp}|))$$

$$+ C_2 V_{DD} (V_{DD} + |V_{tp}|)$$

$$= f P_A^2 P_B^2 P_C (1 - P_A)$$

$$\times (9.2225 + 94.5 (3 - |V_{tp}|) \times 10^{-15} \text{ watts}$$

$$\text{for } P_A = \frac{1}{2}, P_B = P_C = 1$$

$$\Rightarrow P_{\text{Worst}} = f \times 10^{-15} (9.25 + 68.125 - 28.625 |V_{tp}|)$$

watts

	NAND	NOR	Inverter
I_{DD}	16.5 A ₀	23.5 A ₀	3.5 A ₀

$t_p = 9.75 \text{ Reg} + t_p = 13 \text{ Reg free}$
 $t_{pHL} = 11.25 \text{ Reg free} \quad t_{pLH} = 7.60725 \text{ Reg}$
 $t_{pLH} = 7.60725 \text{ Reg} = t_{pLH} = 18.44 \text{ Reg}$
 $t_p = t_{pLH} = t_{pHL} = 2.53575 \text{ Reg free}$

~~Ex (3.3 15% 5 - 9 uV₀)~~

Largest area for NOR
 smallest for Inverter

power dissipation largest for NOR

and lowest for Inverter

assuming $|V_{th}| = V_{th} \sim 0.5V$

t_{pLH} & t_{pHL} delay min for Inverter

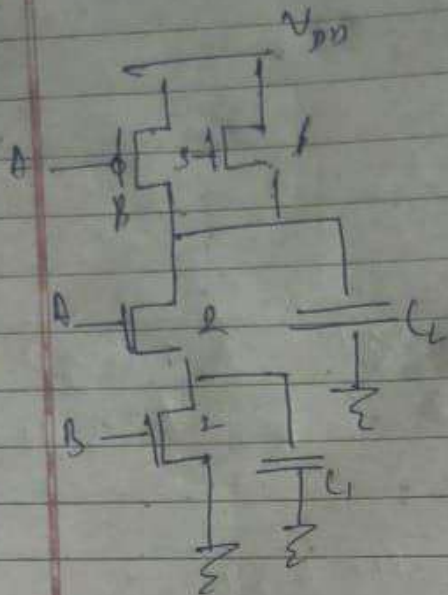
t_{pLH} min for NOR

t_{pHL} min for NAND

t_p smallest for inverter

Ans

NAND



$$I_{DC} = 4A + 2kA_0$$

$$C_L = (2\beta + 2) \gamma C_{g0}$$

$$C_L = (2 + 2) \gamma C_{g0} = 4 \gamma C_{g0}$$

A	B	P	Probability
0	0	1	$\bar{P}_A \bar{P}_B$
0	1	1	$\bar{P}_A P_B$
1	0	1	$P_A \bar{P}_B$
1	1	1	$P_A P_B$

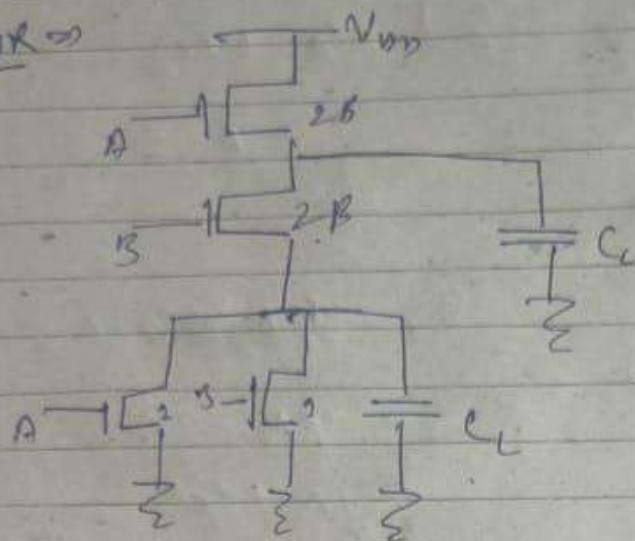
$$\begin{cases} 3 \text{ cases} \\ A = B = 1 \rightarrow A = B = 0 \\ A = B = 1 \rightarrow A = 0, B = 1 \\ A = B = 1 \rightarrow A = 1, B = 0 \end{cases}$$

$$\begin{aligned} \text{Total } P_{dynamic} &= f \times (P_{A=0} P_{B=0}) (\bar{P}_A \bar{P}_B C_L V_{DD}^2 \\ &\quad + \bar{P}_A P_B C_L V_{DD}^2 \\ &\quad + P_A \bar{P}_B C_L V_{DD}^2 + P_A P_B C_L V_{DD}^2) \end{aligned}$$

$$\begin{aligned} &= f P_A P_B (\bar{P}_A \bar{P}_B (2\beta + 2) \gamma C_{g0} V_{DD}^2 \\ &\quad + V_{DD}^2 \bar{P}_A P_B (2\beta + 2) \gamma C_{g0} \\ &\quad + P_A \bar{P}_B (2\beta + 2) \gamma C_{g0} V_{DD}^2 \\ &\quad + P_A P_B V_{DD} (V_{DD} - V_{th}) (4 \gamma C_{g0}) \end{aligned}$$

$$\begin{aligned} P_{dyn} &= f (1 - P_A P_B) (P_A P_B) V_{DD}^2 C_L (2 \gamma C_{g0}) \\ &\quad + f (P_A P_B) (P_A (1 - P_B)) (V_{DD} - V_{th}) V_{DD} \end{aligned}$$

NOX \Rightarrow



$$C_L = 2\beta \tau C_{gs} + 2\tau C_{gs} = 2(1+\beta) \tau C_{gs}$$

$$C_1 = 2\beta \tau C_{gs} \times 2 = 4\beta \tau C_{gs}$$

A	B	P	Prob
0	0	1	$\bar{P}_A \bar{P}_B$
1	0	0	$P_A \bar{P}_B$
0	1	0	$\bar{P}_A P_B$
1	1	0	$P_A P_B$

Again 3 cases

$$A=B=1, A=B=0$$

$$A=1, B=0, A=0, B=1$$

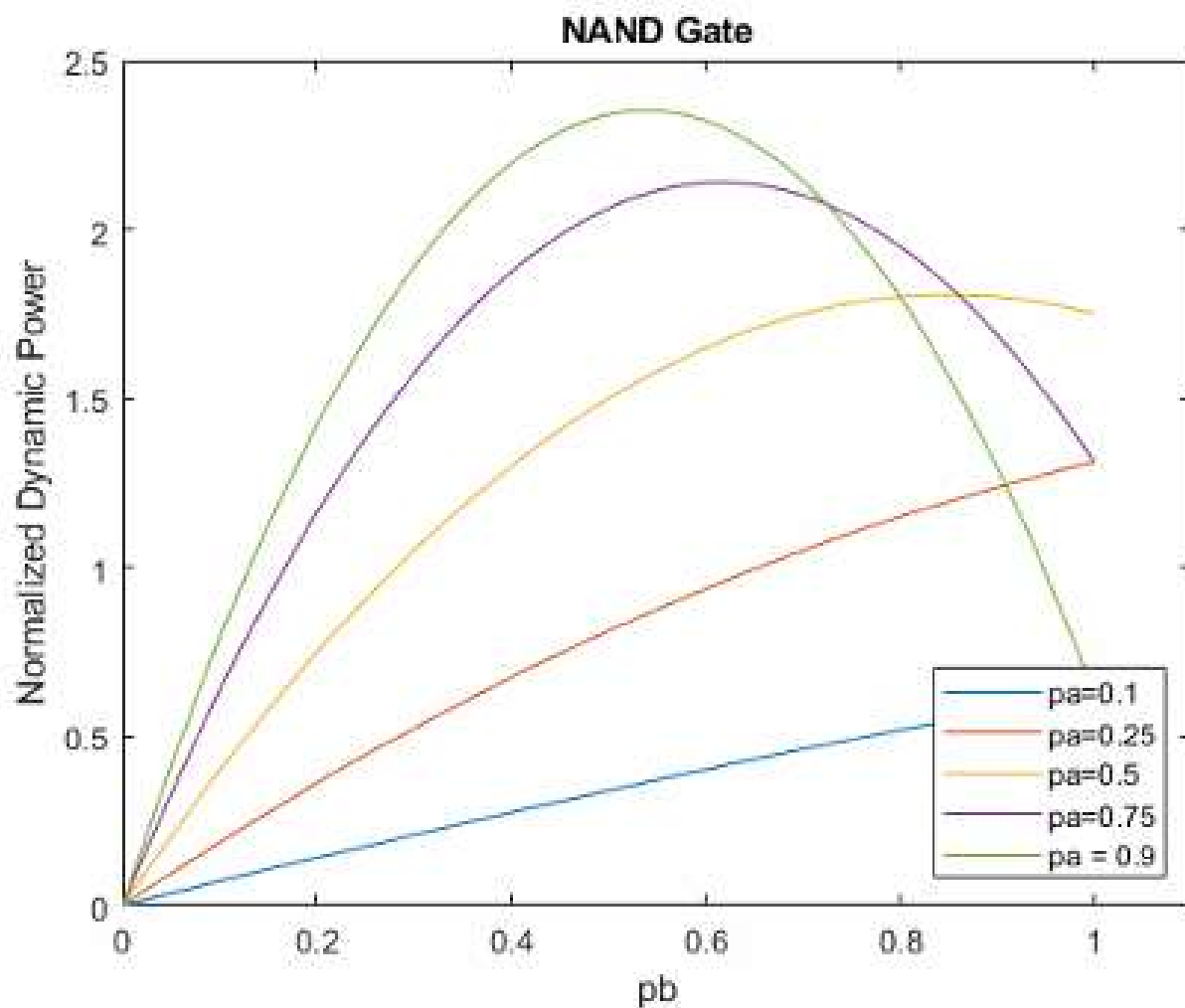
$$A=0, B=1, A=1, B=0$$

$$\begin{aligned} P_{\text{dynamic}} &= f(P_A \bar{P}_B) P_A P_B (C_L V_{DD}^2 + C_L V_{DD} (V_{DD} - |V_{TP}|)) \\ &\quad + f(\bar{P}_A P_B) (\bar{P}_A) (P_B) (C_L V_{DD}^2 + C_L V_{DD} (V_{DD} - |V_{TP}|)) \\ &\quad + f(P_A P_B) \bar{P}_A \bar{P}_B \times C_L \times V_{DD}^2 \\ &\quad + f(\bar{P}_A \bar{P}_B) \bar{P}_A \bar{P}_B \times C_L \times V_{DD}^2 \\ &= f \bar{P}_A P_B (1 - P_A \bar{P}_B) (C_L V_{DD}^2) \\ &\quad + f P_A \bar{P}_B P_B C_L V_{DD} (V_{DD} - |V_{TP}|) \\ &= f P_A P_B (1 - P_A \bar{P}_B) (2 + 2\beta) \tau C_{gs} V_{DD}^2 \\ &\quad + f P_A \bar{P}_A P_B (4\beta \tau C_{gs}) V_{DD} (V_{DD} - |V_{TP}|) \end{aligned}$$


```

%NAND
% Normalizing and assuming certain values where Vth : Vsupply as 1:4
pa = [0.1,0.25,0.5,0.75,0.9];
beta=2.5;
for i = 1:5
    pb = 0:0.01:1;
    dp = pa(i) .* pb .* ((2*beta+2) .* (1-pa(i)) .* (1-pb) + pb .* (1-
pa(i)) .* (2*beta+2) + pa(i) .* (1-pb) .* (2*beta+2) + 4*pa(i) .* (1-
pb) .* (1-0.25));
    plot(pb,dp);
    hold on;
end
legend('pa=0.1','pa=0.25','pa=0.5','pa=0.75','pa =
0.9','Location','southeast')
title('NAND Gate')
xlim([0 1.1])
xlabel('pb')
ylabel('Normalized Dynamic Power')

```



```

%NOR
% Normalizing and assuming certain values where V_th : Vsupply as 1:4
pa = [0.1,0.25,0.5,0.75,0.9];
beta=2.5;
for i = 1:5
    pb = 0:0.01:1;
    dp = (1-pa(i)).*(1-pb).*(1-(1-pa(i)).*(1-
pb)).*(2+2*beta)+pa(i).*(1-pa(i)).*(1-pb).*4.*beta*(1-0.25);
    plot(pb,dp);
    hold on;
end
legend('pa=0.1','pa=0.25','pa=0.5','pa=0.75','pa =
0.9','Location','southeast')
title('NOR Gate')
xlim([0 1])
xlabel('pb')
ylabel('Normalized Dynamic Power')

```

